

Features

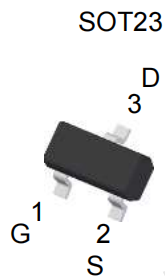
- $V_{DS} = 30V, I_D = 3A$
 $R_{DS(ON)} < 100m\Omega @ V_{GS}=4.5V$
 $R_{DS(ON)} < 130m\Omega @ V_{GS}=10V$

Typical Applications

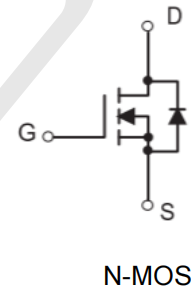
- Load switch
- PWM application

Shipping Quantity

- 3000pcs / Tape & Reel



Circuit Diagram



Marking: J7TPM

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	3	A
Drain Current-Pulsed ^(Note 1)	I_{DM}	20	A
Maximum Power Dissipation	P_D	0.9	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^\circ\text{C}$

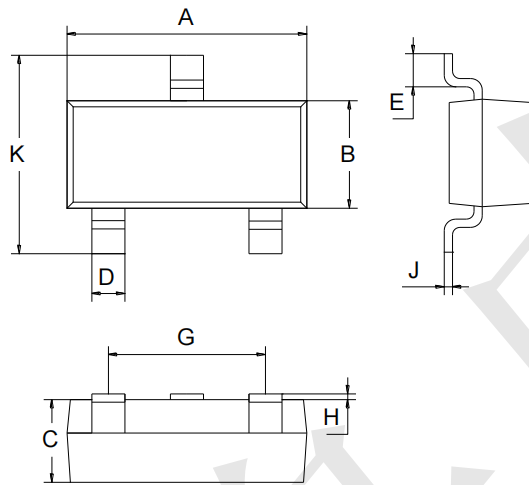
Thermal Characteristic

Thermal Resistance, Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	138	$^\circ\text{C/W}$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

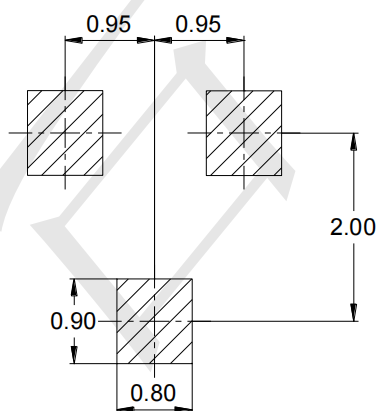
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	3.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A	-	70	100	mΩ
		V _{GS} =4.5V, I _D =2 A	-	95	130	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =3A	14	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =10V, V _{GS} =0V, F=1.0MHz	-	235	-	PF
Output Capacitance	C _{OSS}		-	35	-	PF
Reverse Transfer Capacitance	C _{rss}		-	18	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V, I _D =1A V _{GS} =10V, R _{GEN} =6Ω	-	3.5	-	nS
Turn-on Rise Time	t _r		-	1.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	17.5	-	nS
Turn-Off Fall Time	t _f		-	2.5	-	nS
Total Gate Charge	Q _g	V _{DS} =15V, I _D =3A, V _{GS} =10V	-	10	-	nC
Gate-Source Charge	Q _{gs}		-	0.95	-	nC
Gate-Drain Charge	Q _{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	3	A

Outline Drawing - SOT23



SOT-23		
Dimension	Min.	Max.
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60

Land Pattern - SOT23



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